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Team Nexperia

**Product data sheet** 

## 1. Product profile

### 1.1 General description

PNP medium power transistors in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package	NPN complement		
	NXP	JEITA	JEDEC	
BCP53T	SOT223	SOT223 SC-73	-	BCP56T
BCP53-10T				BCP56-10T
BCP53-16T				BCP56-16T

#### 1.2 Features and benefits

- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- Three current gain selections
- High power dissipation capability
- AEC-Q101 qualified

### 1.3 Applications

- Linear voltage regulators
- MOSFET drivers
- High-side switches
- Power management
- Amplifiers

## 1.4 Quick reference data

Table 2. Quick reference data

 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-80	V
I <sub>C</sub>	collector current		-	-	-1	Α
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-	-2	Α



Table 2. Quick reference data ...continued

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
h <sub>FE</sub>	DC current gain	$V_{CE} = -2 \text{ V}; I_{C} = -150 \text{ mA}$	63	-	250	
	BCP53-10T	$V_{CE} = -2 \text{ V}; I_{C} = -150 \text{ mA}$ [1]	63	-	160	
	BCP53-16T	$V_{CE} = -2 \text{ V}; I_{C} = -150 \text{ mA}$ [1]	100	-	250	

<sup>[1]</sup> Pulse test:  $t_p \le 300 \ \mu s; \ \delta = 0.02$ 

## 2. Pinning information

Table 3. Pinning

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		6
2	С	collector	4	J
3	E	emitter		В
4	С	collector		E sym132

# 3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
BCP53T	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223
BCP53-10T			
BCP53-16T			

# 4. Marking

Table 5. Marking codes

Type number	Marking code
BCP53T	BCP53T
BCP53-10T	P5310T
BCP53-16T	P5316T

## 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-100	V
$V_{CEO}$	collector-emitter voltage	open base		-	-80	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
I <sub>C</sub>	collector current			-	-1	А
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	-2	Α
I <sub>B</sub>	base current			-	-0.2	А
I <sub>BM</sub>	peak base current	single pulse; $t_p \le 1 \text{ ms}$		-	-0.3	A
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u>	-	0.6	W
			[2]	-	1	W
			[3]	-	1.3	W
			[4]	-	1.3	W
			<u>[5]</u>	-	1.8	W
Tj	junction temperature			-	+150	°C
T <sub>amb</sub>	ambient temperature			-55	+150	°C
T <sub>stg</sub>	storage temperature			-65	+150	°C

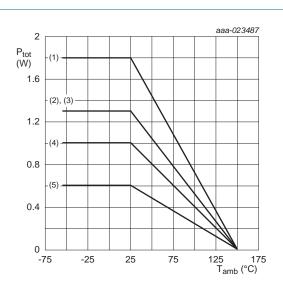
<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>.

<sup>[3]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 6 cm<sup>2</sup>.

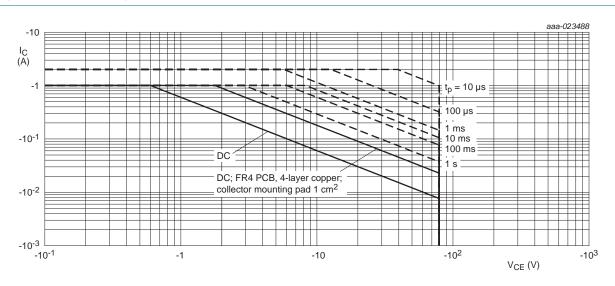
<sup>[4]</sup> Device mounted on an FR4 PCB, 4-layer copper; tin-plated and standard footprint.

<sup>[5]</sup> Device mounted on an FR4 PCB, 4-layer copper; tin-plated; mounting pad for collector 1 cm<sup>2</sup>.



- (1) FR4 PCB, 4-layer copper, 1 cm<sup>2</sup>
- (2) FR4 PCB, single-sided copper, 6 cm<sup>2</sup>
- (3) FR4 PCB, 4-layer copper, standard footprint
- (4) FR4 PCB, single-sided copper, 1 cm<sup>2</sup>
- (5) FR4 PCB, single-sided copper, standard footprint

Fig 1. Power derating curves



Unless otherwise specified:

T<sub>amb</sub> = 25 °C

Single pulse

FR4 PCB, single-sided copper; standard footprint

Fig 2. Safe operating area; junction to ambient; continuous and peak collector currents as a function of collector-emitter voltage

### 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	209	K/W
			[2]	-	-	125	K/W
			[3]	-	-	97	K/W
			[4]	-	-	97	K/W
			[5]	-	-	70	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	18	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on an FR4 PCB, 4-layer copper; tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, 4-layer copper; tin-plated; mounting pad for collector 1 cm<sup>2</sup>.

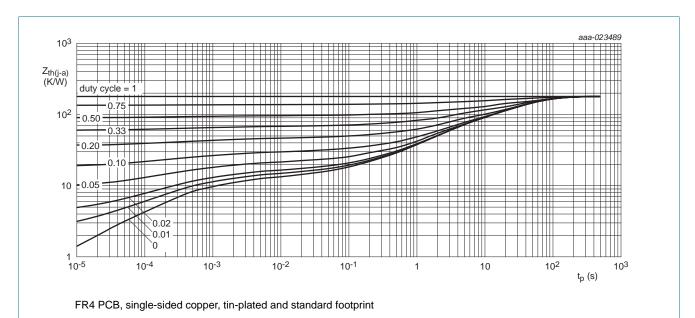
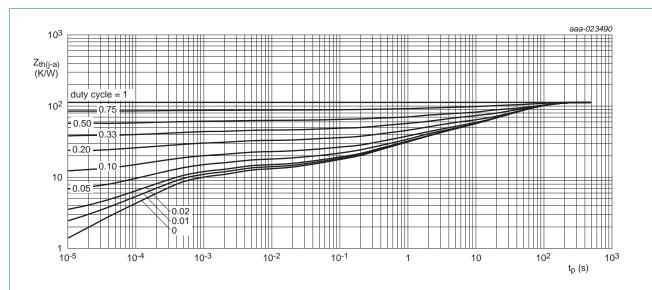
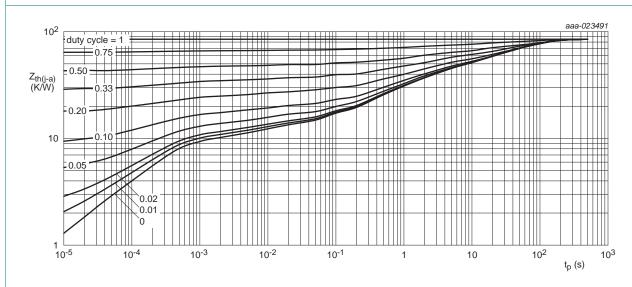


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



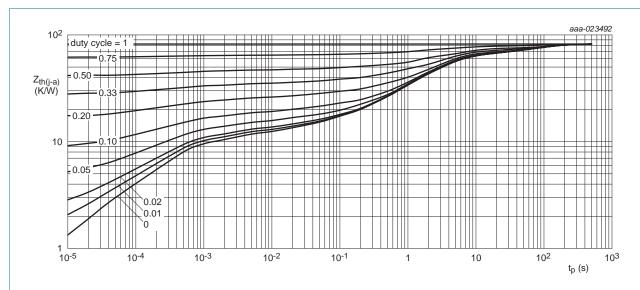
FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



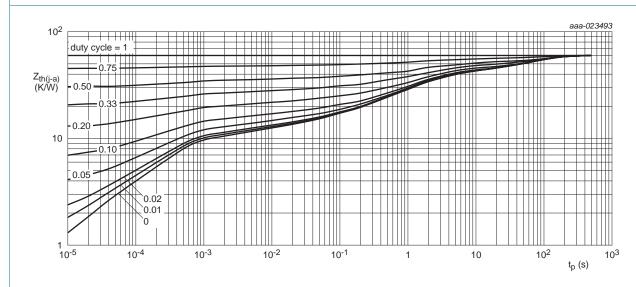
FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 6 cm<sup>2</sup>

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, tin-plated and standard footprint.

Fig 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>

Fig 7. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

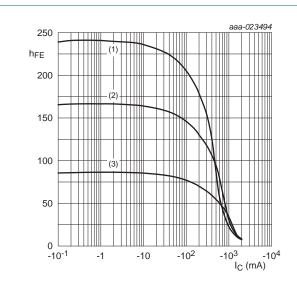
## 7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}$		-	-	-100	nA
	current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$		-	-	-10	μА
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$		-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -2 \text{ V}; I_{C} = -5 \text{ mA}$		63	-	-	
		$V_{CE} = -2 \text{ V}; I_{C} = -150 \text{ mA}$	[1]	63	-	250	
		$V_{CE} = -2 \text{ V}; I_{C} = -500 \text{ mA}$	[1]	40	-	-	
	BCP53-10T	$V_{CE} = -2 \text{ V}; I_{C} = -150 \text{ mA}$	[1]	63	-	160	
	BCP53-16T	$V_{CE} = -2 \text{ V}; I_{C} = -150 \text{ mA}$	<u>[1]</u>	100	-	250	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$	<u>[1]</u>	-	-	-500	mV
$V_{BE}$	base-emitter voltage	$V_{CE} = -2 \text{ V}; I_{C} = -500 \text{ mA}$	<u>[1]</u>	-	-	-1	V
f⊤	transition frequency	$V_{CE} = -5 \text{ V; } I_{C} = -50 \text{ mA;}$ f = 100 MHz		100	140	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz		-	7	-	pF

<sup>[1]</sup> Pulse test:  $t_p \le 300 \ \mu s; \ \delta = 0.02$ 



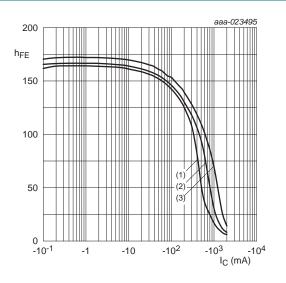
$$V_{CE} = -2 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 8. DC current gain as a function of collector current; typical values



(1) 
$$V_{CE} = -1 V$$

(2) 
$$V_{CE} = -2 V$$

(3)  $V_{CE} = -5 \text{ V}$ 

Fig 9. DC current gain as a function of collector current; typical values

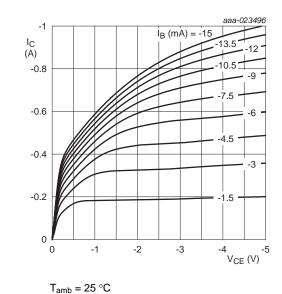
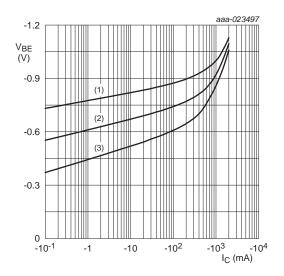


Fig 10. Collector current as a function of collector-emitter voltage; typical values



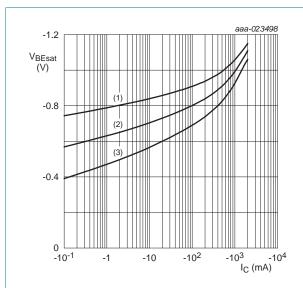
$$V_{CE} = -2 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig 11. Base-emitter voltage as a function of collector current; typical values



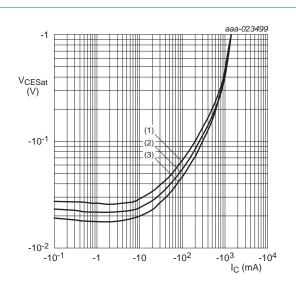
$$I_{\rm C}/I_{\rm B} = 10$$

(1) 
$$T_{amb} = -55 \,^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig 12. Base-emitter saturation voltage as a function of collector current; typical values



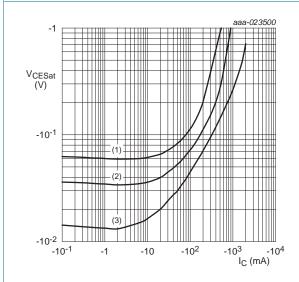
$$I_{\rm C}/I_{\rm B} = 10$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 13. Collector-emitter saturation voltage as a function of collector current; typical values



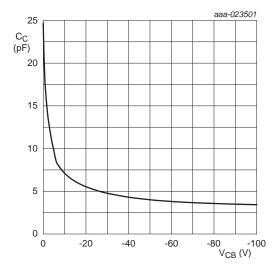
T<sub>amb</sub> = 25 °C

(1) 
$$I_C/I_B = 50$$

(2) 
$$I_C/I_B = 20$$

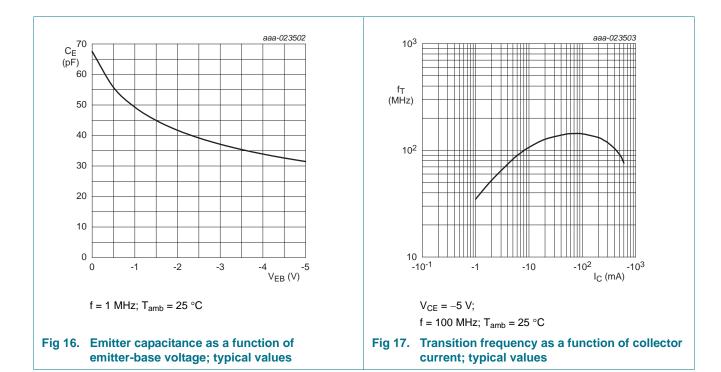
(3)  $I_C/I_B = 5$ 

Fig 14. Collector-emitter saturation voltage as a function of collector current; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$ 

Fig 15. Collector capacitance as a function of collector-base voltage; typical values

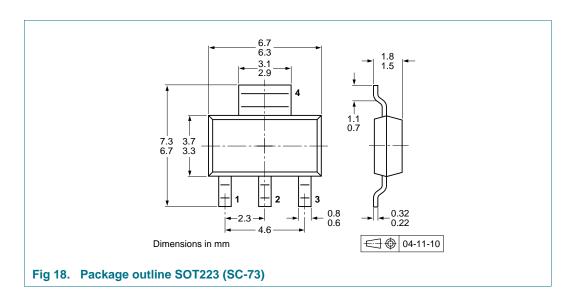


## 8. Test information

## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 9. Package outline

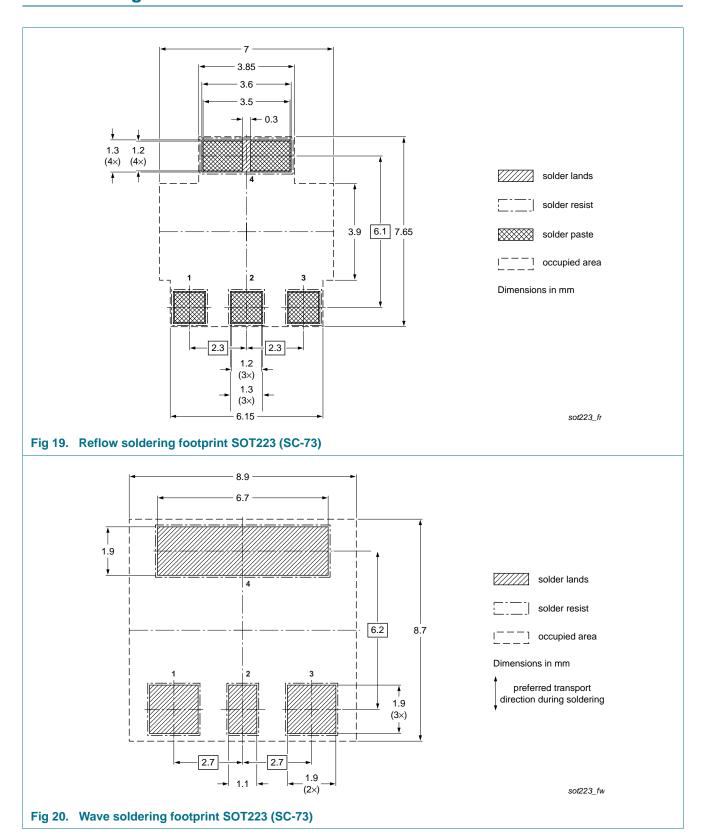


BCP53T\_SER

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## 10. Soldering





# 11. Revision history

### Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BCP53T_SER v.1	20160705	Product data sheet	-	-

## 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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## **BCP53T series**

### 80 V, 1 A PNP medium power transistors

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# **BCP53T series**

## 80 V, 1 A PNP medium power transistors

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